

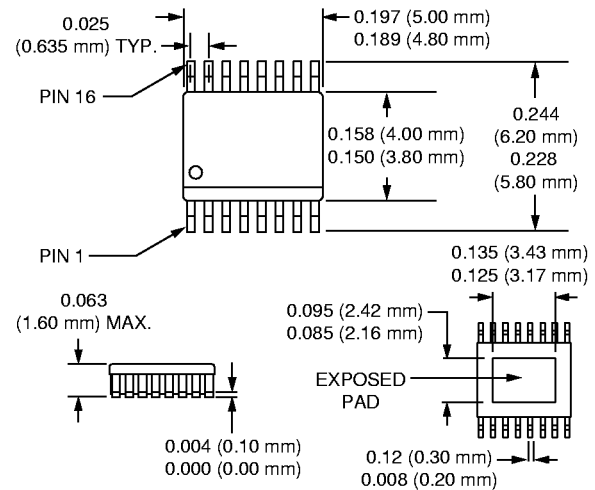
3.5 V Dual-Band GSM Power Amplifier


AP116-89

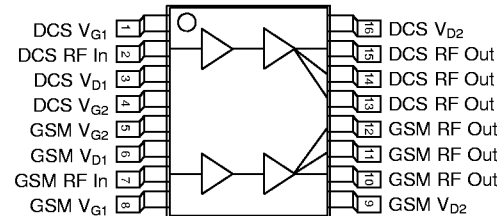
Features

- Dual-Band GSM 900 MHz and DCS1800 MHz Amplifier in a Single Package
- Low Voltage Operation for Next Generation Handsets
- Power Added Efficiency of 55%
- Wide Power Control Range (50 dB)
- External Matching Elements Optimize Performance for Either DCS1800 MHz or DCS1900 MHz Bands
- Thermally Enhanced Package

SSOP-16 with Exposed Pad



Pin Out



GSM Operating Characteristics at 25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Output Power	P _{OUT}	V _{GG} = -1.5 V	34.5	35		dBm
	P _{OUT}	V _{DS} = 2.8 V	32.1			dBm
Power Added Efficiency	PAE		48	55		%
Return Loss	RL				-10	dB
Power Down	P _{OUT}	V _{GG} = -3 V		-15	-10	dBm

Unless otherwise stated, V_{D1} = V_{D2} = 3.5 V, input power = +12 dBm, frequency = 900 MHz.

DCS Operating Characteristics at 25°C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Output Power	P _{OUT}	V _{GG} = -1.5 V	32.5	33		dBm
	P _{OUT}	V _{DS} = 2.8 V	30.2			dBm
Power Added Efficiency	PAE		40	45		%
Return Loss	RL				-10	dB
Power Down	P _{OUT}	V _{GG} = -3 V		-15	-10	dBm

Unless otherwise stated, V_{D1} = V_{D2} = 3.5 V, input power = +14 dBm, frequency = 1785 MHz.